
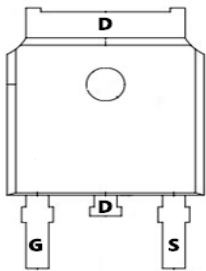




TMGN10050AD

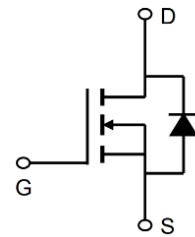
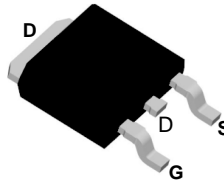
N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 100V$ $I_D = 50A$</p> <p>$R_{DS(ON)} = 20\text{ m}\Omega(\text{typ.}) @ V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Marking: G50N10

D:TO-252-3L



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	50 A
		$T_C = 100^\circ\text{C}$	30 A
I_{DM}	Pulsed Drain Current ^{note1}	150	A
EAS	Single Pulsed Avalanche Energy ^{note2}	62.6	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	73	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.0	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$



TMGN10050AD

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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=10V, I_D=20A$	-	20	30	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	24	34	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	3727	-	pF
C_{oss}			-	80	-	pF
C_{rss}	Reverse Transfer Capacitance		-	148	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=15A,$ $V_{GS}=10V$	-	40	-	nC
Q_{gs}	Gate-Source Charge		-	6.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	28	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V, I_D=15A,$ $R_G=1.8\Omega, V_{GS}=10V$	-	22	-	ns
t_r	Turn-on Rise Time		-	182	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	80	-	ns
t_f	Turn-off Fall Time		-	142	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	150	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=30A, di/dt=100A/\mu s$	-	71	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	145	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^\circ\text{C}$, $V_{DD}=50V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$, $I_{AS}=14.5A$ 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

Figure 1: Output Characteristics

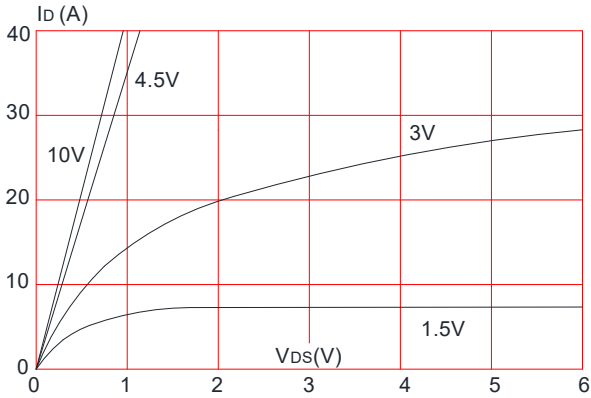


Figure 2: Typical Transfer Characteristics

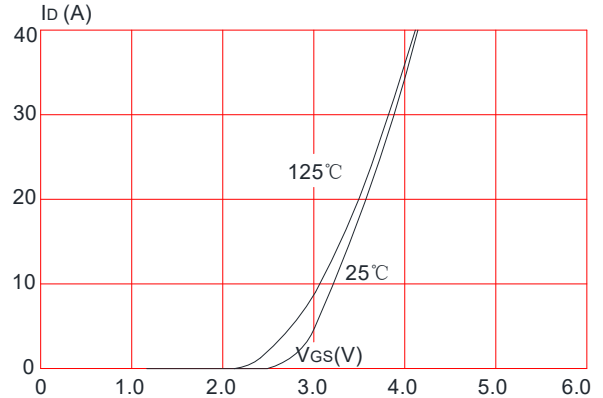


Figure 3: On-resistance vs. Drain Current

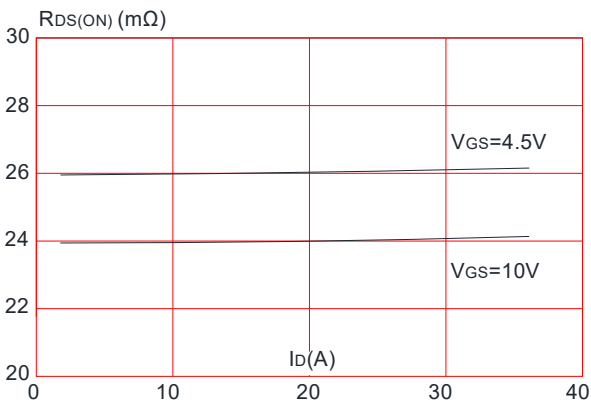


Figure 4: Body Diode Characteristics

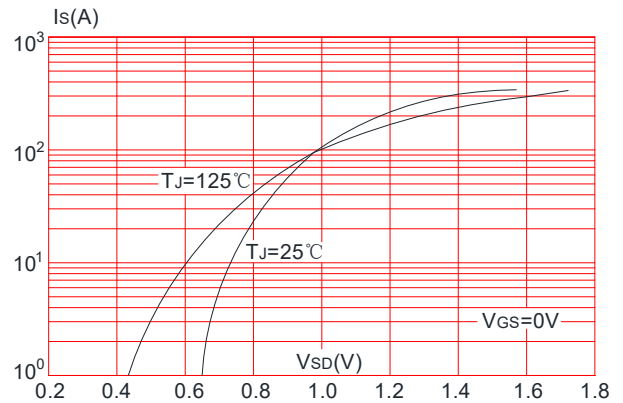


Figure 5: Gate Charge Characteristics

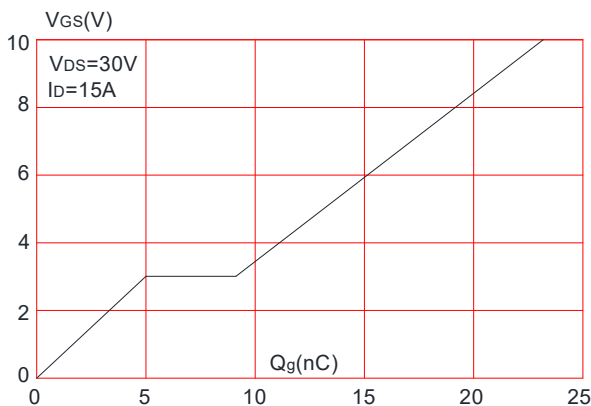
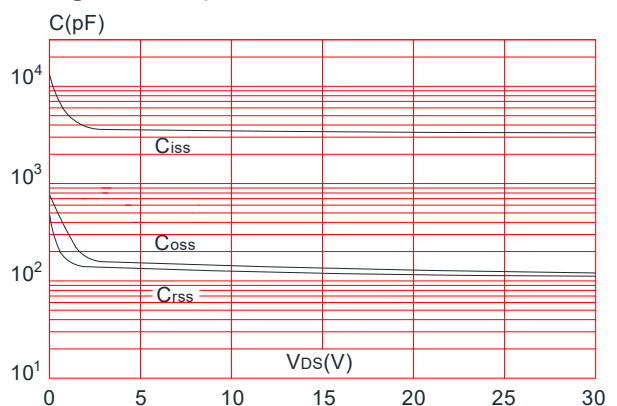


Figure 6: Capacitance Characteristics



N-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

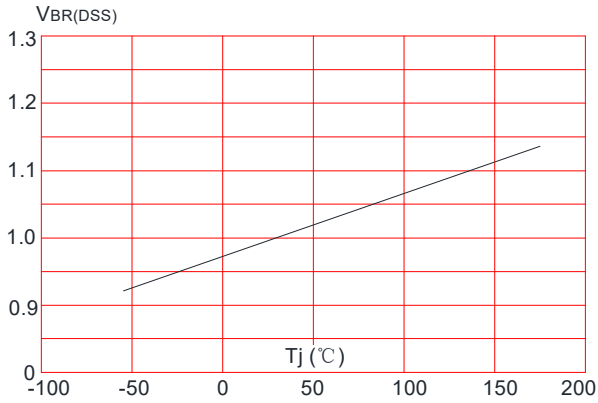


Figure 8: Normalized on Resistance vs. Junction Temperature

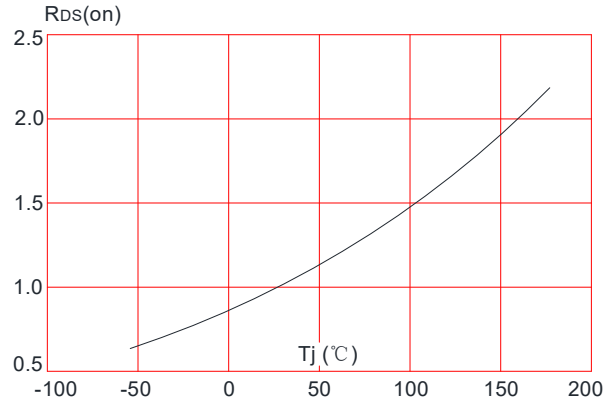


Figure 9: Maximum Safe Operating Area

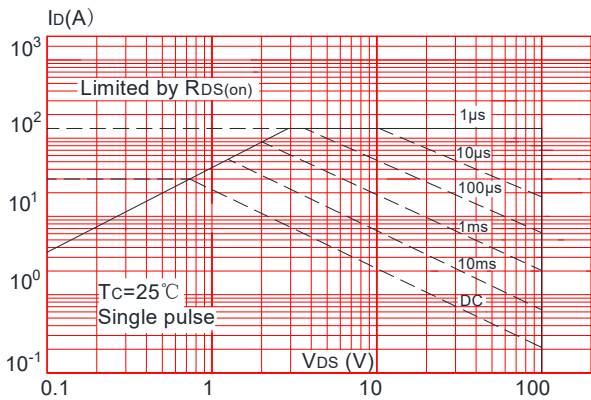


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

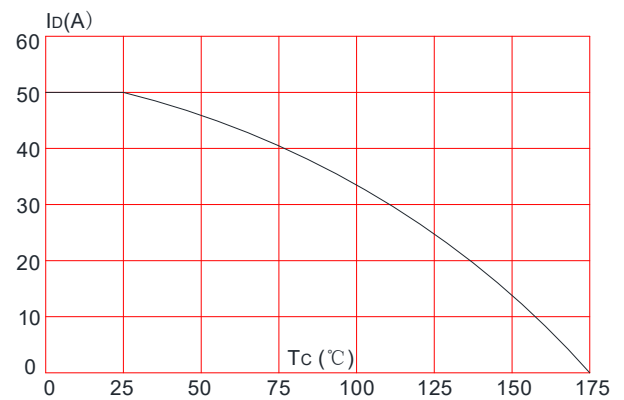
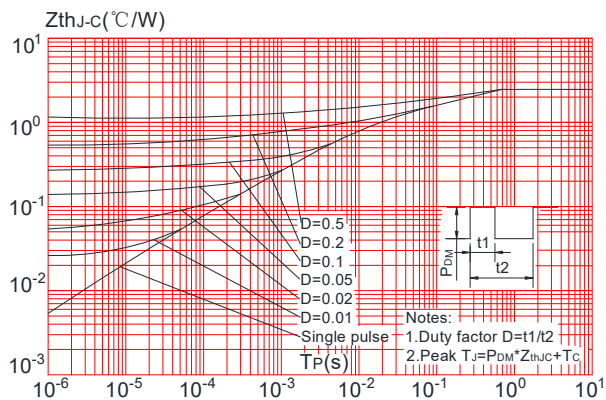
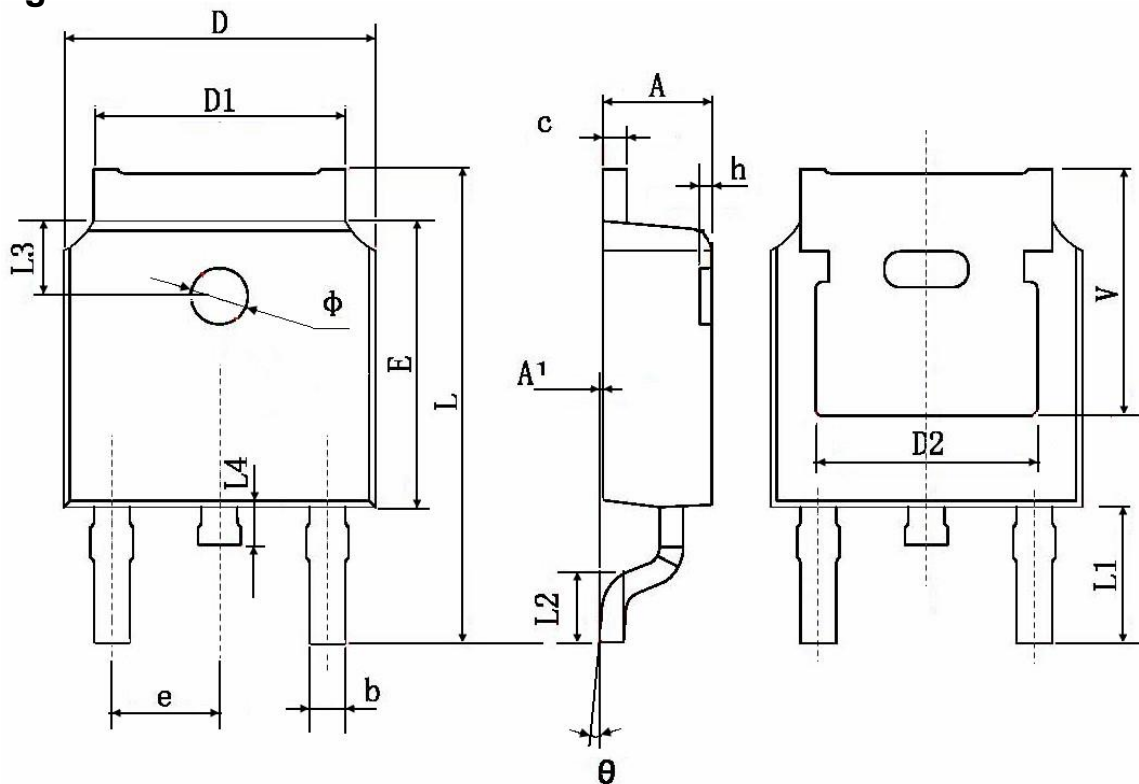


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Package Information: TO-252-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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